

Voltage Gain:  $A_v = \frac{v_o}{v_i}$

Current Gain:  $A_i = \frac{i_o}{i_i}$

Power Gain:  $G = A_v A_i$

Decibel:  $A_{v\text{dB}} = 20 \log(|A_v|)$

$A_{i\text{dB}} = 20 \log(|A_i|)$

$G_{\text{dB}} = 10 \log(|G|)$

<p>Energy Conservation: <math>P_i + P_s = P_o + P_d \longrightarrow \begin{cases} P_i &amp; = \text{Power from Source} \\ P_s &amp; = \text{Power from DC Supplies} \\ P_o &amp; = \text{Output Power at Load} \\ P_d &amp; = \text{Power Dissipated in the Op-Amp} \end{cases}</math></p>
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Frequency Dependence:

Capacitor:  $Z_c = \frac{1}{j\omega C}$

Inductor:  $Z_L = j\omega L$

Summing Point Constraint:

- Only applies when the op-amp is in negative feedback
- Assuming ideal op-amp,  $V_+ - V_- = 0$  (no current at terminals)
- For non-ideal op-amps:  $V_o = A(s)(V_+ - V_-)$

$f_{3\text{dB}} = \frac{\omega_{3\text{dB}}}{2\pi}$

$\text{GBW} = |A_v| f_{3\text{dB}}$

Diodes:

- In Forward Bias (FB): Permit current flow, have a positive voltage drop
- In Reverse Bias (RB): No current flow (open circuit)
  - Constant Voltage Drop (CVD): Diodes have same forward-bias drop ( $\approx .7\text{V}$ )
- Assume bias mode for each diode in diagram, calculate values to verify assumptions
- CVD + resistance model:  $r_d = \frac{nV_T}{I_{DQ}}$  (approximated around quiescent point,  $Q$ )

$I_D = I_s e^{\frac{V_D}{nV_T}} + 1$       Room Temp:  $V_T \approx 26\text{mV}$        $1 < n < 2$        $10^{-6} < I_s < 10^{-18}\text{A}$

Temp Dependence: constant $I \rightarrow V$ drop decreases $\approx 2\text{mV}$ per $1^\circ\text{C}$ temperature increase
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Zener Diodes:  $V_D = -V_{zo} - I_z r_z$  in breakdown, with  $I_z = -I_D > 0$

Transformers: step voltages according to turns ratio ( $N_p : N_s$ ) or ( $n : 1$ ), with  $V_s = V_p/n$

BJT Regions

EBJ	CBJ	Mode
FB	RB	Active
FB	FB	Saturation
RB	RB	Cutoff

Note: When designing an amplifier confirm that the BJT is in the active region

BJT Formulas

$$I_E = I_C + I_B$$

$$I_E = I_{ES} \left[ e^{\frac{V_{BE}}{V_T}} - 1 \right]$$

Active Region Only:

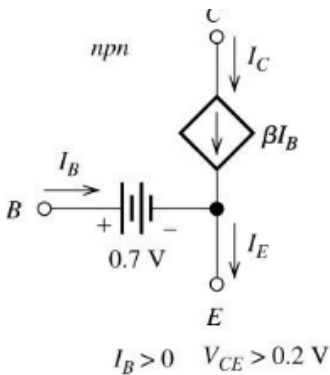
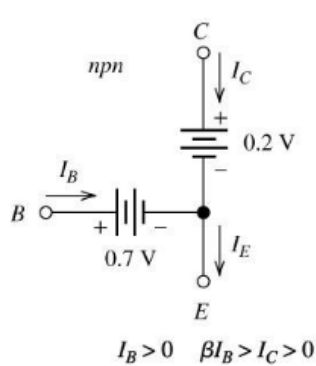
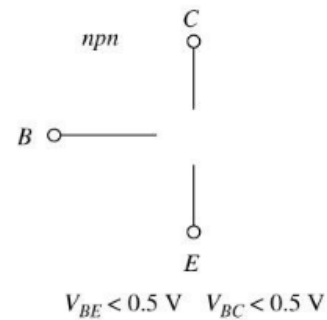
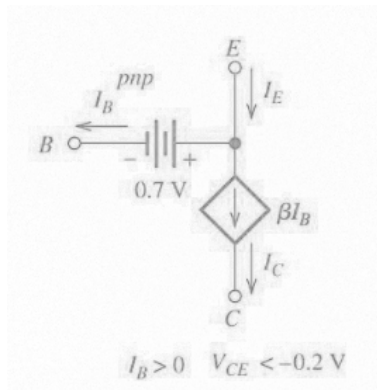
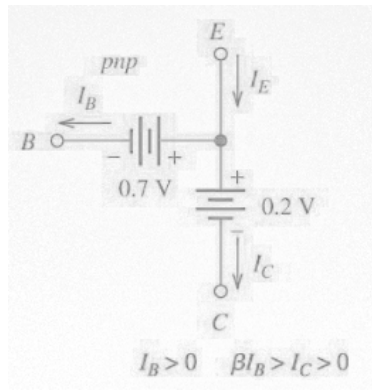
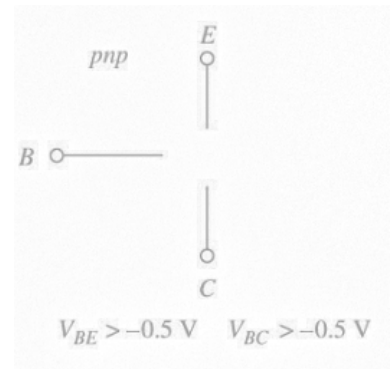
$$I_C = \alpha I_E$$

$$I_B = (1 - \alpha) I_E$$

$$I_C = \beta I_B$$

$$I_S = \alpha I_{ES}$$

For BJTs:	$\beta = \frac{\alpha}{1 - \alpha}$	$\alpha = \frac{\beta}{1 + \beta}$	Typically: $\alpha \approx 1$ , and $I_C \approx I_E$ but $I_C < I_E$
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BJT ModelsFigure 1: *npn* in Active ModeFigure 2: *npn* in SaturationFigure 3: *npn* in CutoffFigure 4: *pnp* in Active ModeFigure 5: *pnp* in SaturationFigure 6: *pnp* in Cutoff

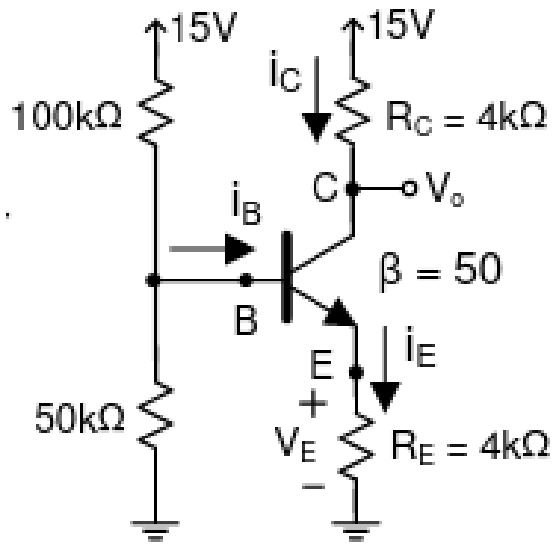


Figure 7: Initial Circuit

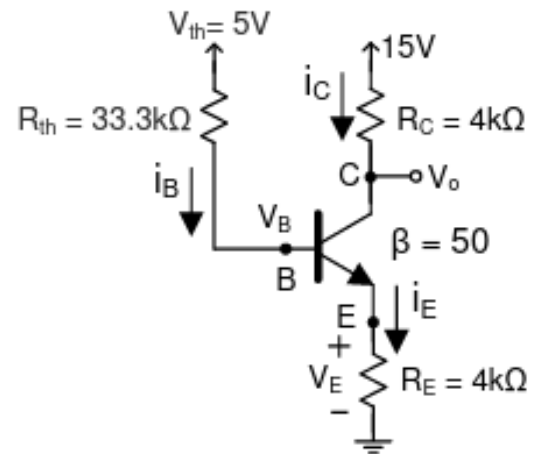


Figure 8: Thévenin Equivalent